

Name \_\_\_\_\_

EE40

Midterm 3

April 24, 2003

**PLEASE WRITE YOUR NAME ON EACH ATTACHED PAGE**

**PLEASE SHOW YOUR WORK TO RECEIVE PARTIAL CREDIT**

**PLEASE DO NOT LEAVE UNTIL EXAM PERIOD IS OVER**

Problem 1: 15 Points Possible \_\_\_\_\_

Problem 2: 20 Points Possible \_\_\_\_\_

Problem 3: 15 Points Possible \_\_\_\_\_

Problem 4: 20 Points Possible \_\_\_\_\_

Problem 5: 20 Points Possible \_\_\_\_\_

Problem 6: 10 Points Possible \_\_\_\_\_

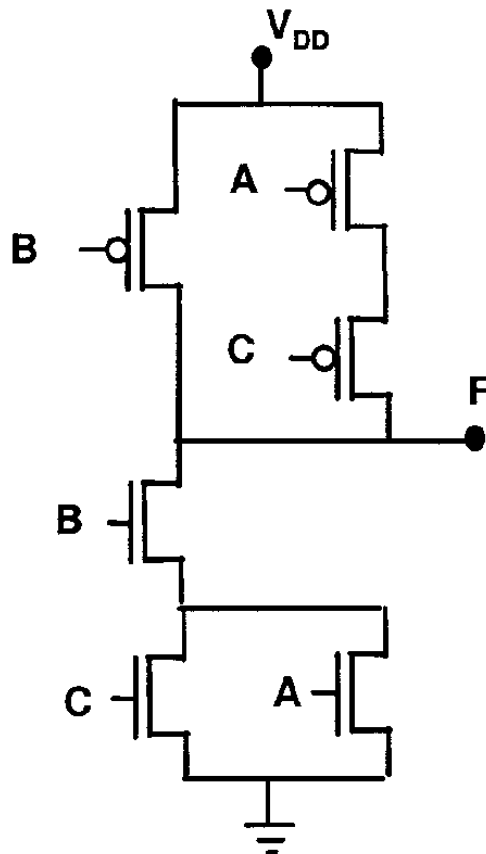
TOTAL: 100 Points Possible \_\_\_\_\_

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**Problem 1:** 15 Points Possible

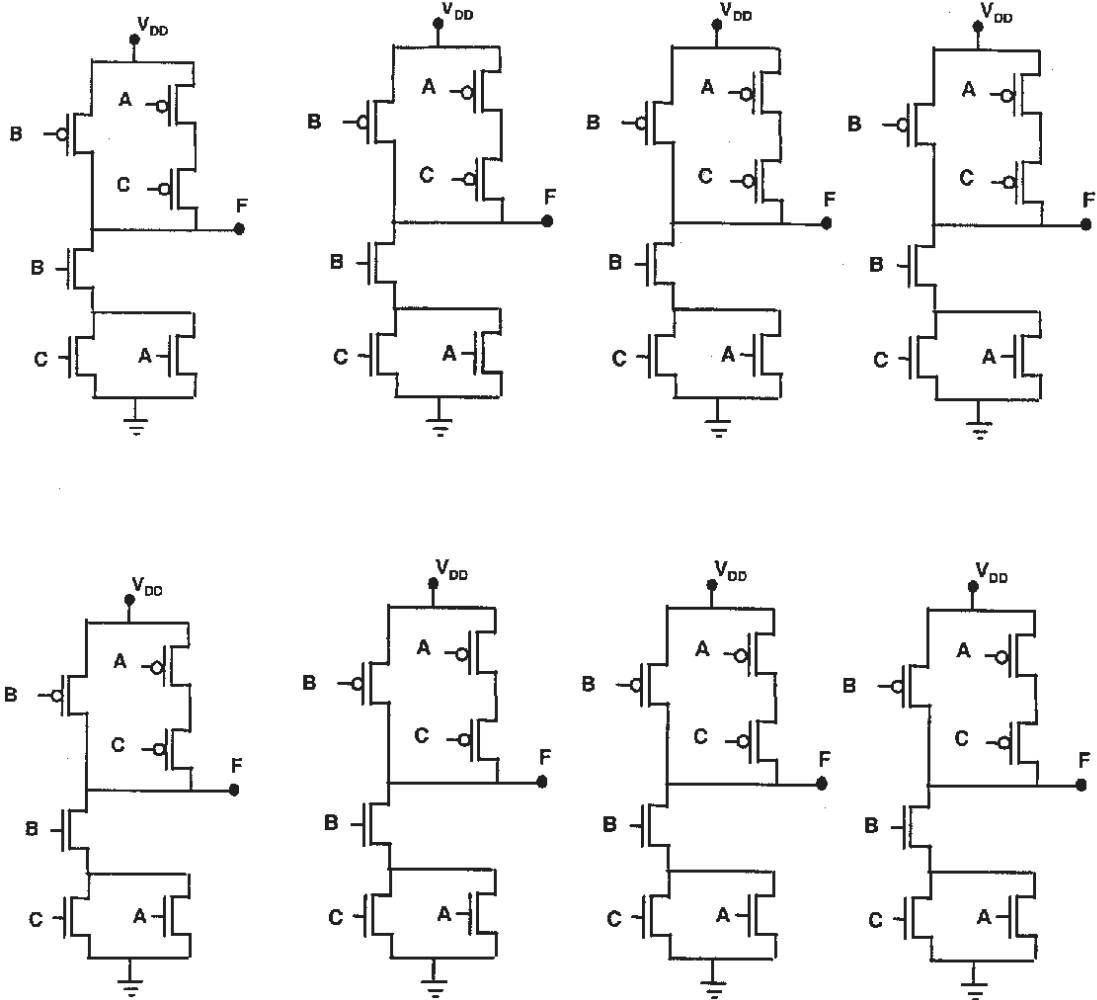
Determine whether the circuit below performs a logical operation. If it does, give the Boolean function it computes. If not, give a set of inputs that results in an invalid output.

For your convenience, 8 copies of this circuit are given on the next page. Assume that all PMOS transistors have source terminal on top, and all NMOS transistors have source terminal on the bottom.



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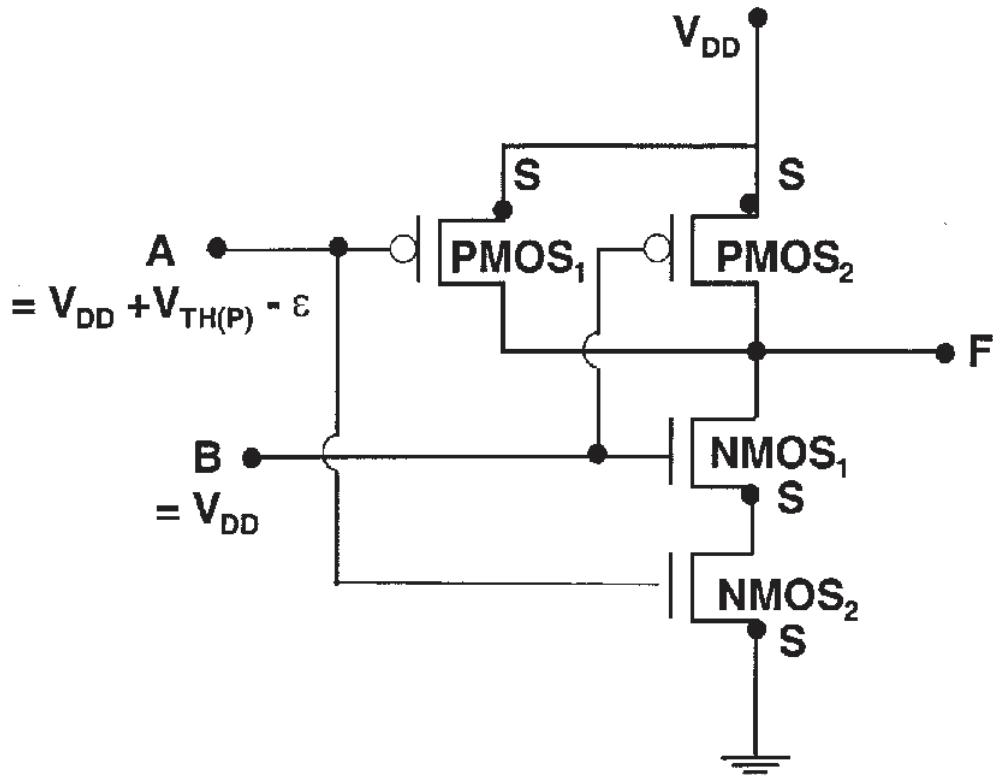
**Problem 1 Workspace**



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**Problem 2:** 20 Points Possible

For the CMOS logic circuit below, determine the most probable mode of operation for each transistor. Assume that  $\epsilon$  is a very small positive number, and  $V_{DD}$  is much larger in magnitude than either  $V_{TH}$ .



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**Problem 3:** 15 Points Possible

Consider the inverter at right, which turns on an LED when the output voltage is high.

I have put a resistor in series with the LED to limit the current so the LED doesn't burn.

But, the LED needs a current of at least 20 mA to light up.

I want the LED to light up for an input voltage as high as 0.8 V.

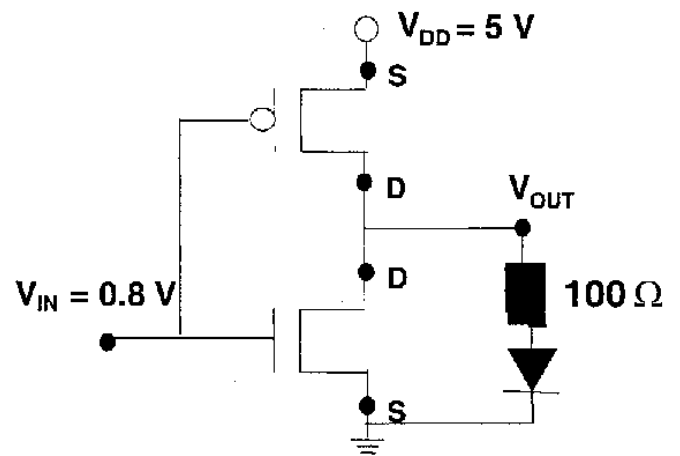
Will the LED light up for an input of 0.8 V?

$W/L \mu C_{OX} = 100 \text{ mA/V}^2$  for both transistors,

$V_{TH(N)} = -V_{TH(P)} = 1 \text{ V}$ ,

$\lambda = 0 \text{ V}^{-1}$  for both transistors,

$V_F = 2 \text{ V}$  for the LED (use large-signal model).



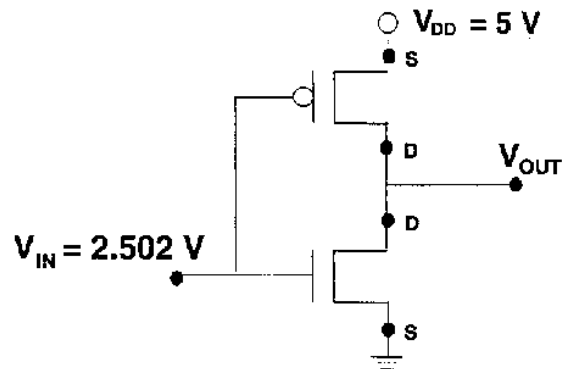
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**Problem 4:** 20 Points Possible

Consider the CMOS inverter at right, with

$W/L \mu C_{OX} = 1 \text{ mA/V}^2$  for both transistors,  
 $V_{TH(N)} = -V_{TH(P)} = 1 \text{ V}$ ,  
 $\lambda = 0.01 \text{ V}^{-1}$  for both transistors.

For this inverter,  $V_M = 2.5 \text{ V}$ .



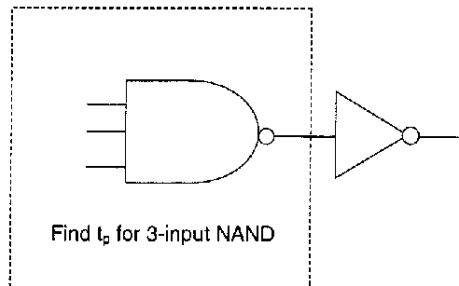
- Find  $V_{OUT}$  for  $V_{IN} = 2.502 \text{ V}$ . Hint for guessing modes: Notice that  $V_{IN}$  is close to  $V_M$ .
- Find the slope of the  $V_{OUT}$  vs.  $V_{IN}$  curve in this region, given by

$$\frac{\Delta V_{OUT}}{\Delta V_{IN}} = \frac{V_{OUT}(\text{for } V_{IN} = 2.502 \text{ V}) - V_M}{2.502 \text{ V} - V_M}$$

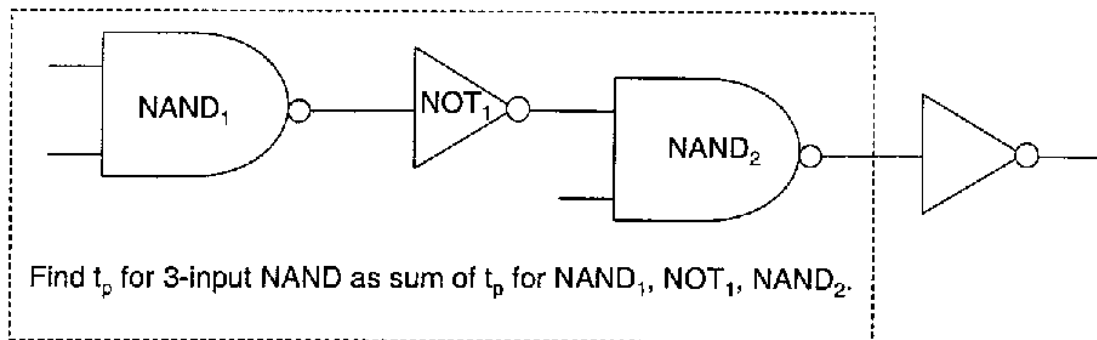
Name \_\_\_\_\_

**Problem 5:** 20 Points Possible

Find the propagation delay for this 3-input NAND gate with inverter load,



where the 3-input NAND is implemented using two 2-input NAND gates and an inverter:



Compute the propagation delay  $t_p$  for the 3-input NAND as the sum of the worst-case propagation delays of the individual gates inside.

Use  $R_N = 1 \text{ k}\Omega$ ,  $R_P = 2 \text{ k}\Omega$ , and  $C_G = 10 \text{ fF}$  per transistor. Ignore interconnect capacitance.

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**Problem 6:** 10 Points Possible

Design a circuit, using only NMOS and PMOS transistors (and a power supply), that performs the 3-input NAND function with **shorter** worst-case propagation delay than the implementation given in Problem 5, when a single inverter is attached as the output load.

Assume that your transistors have the same characteristics as those in Problem 5.

Use  $R_N = 1 \text{ k}\Omega$ ,  $R_P = 2 \text{ k}\Omega$ , and  $C_G = 10 \text{ fF}$  per transistor. Ignore interconnect capacitance.

Provide your design and its worst-case propagation delay with single inverter output load.



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**Fun Corner**

It's picture time again! If you finish early, please don't get up and disturb students in your row. Instead, show off your artistic/comedic ability here.

